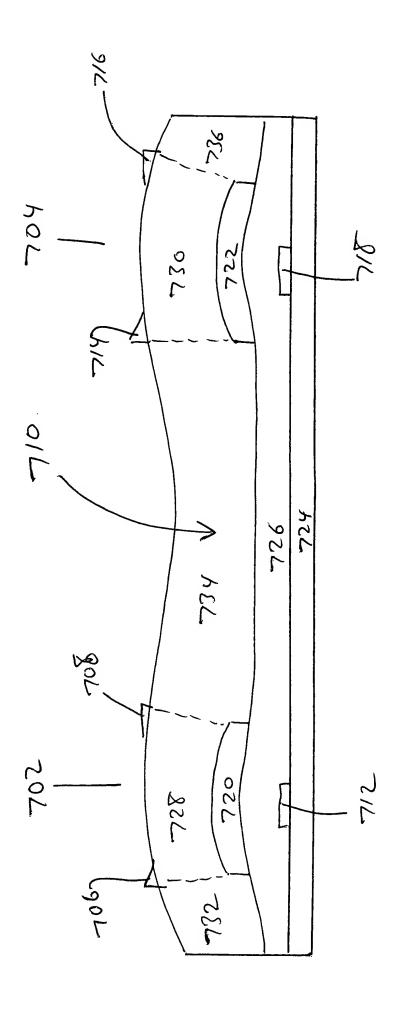
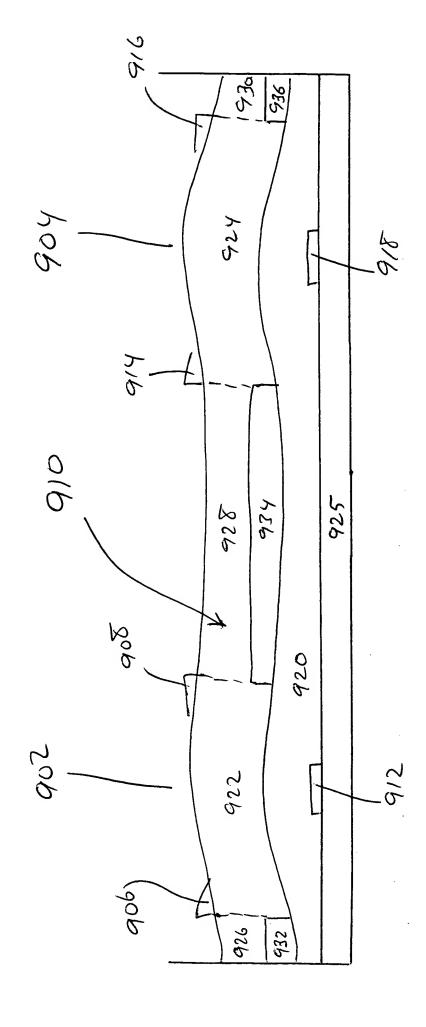


A6.6

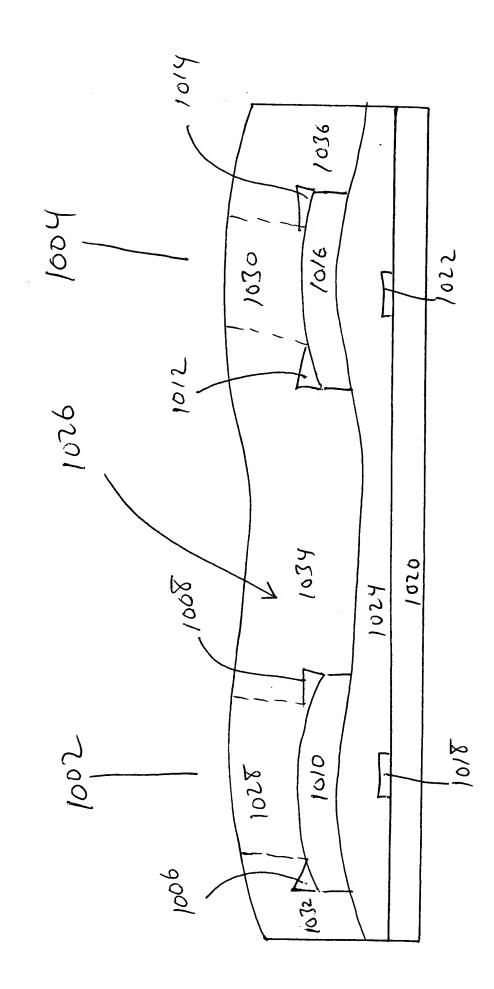
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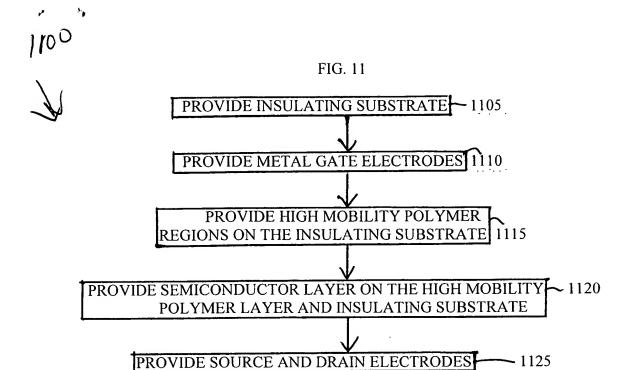


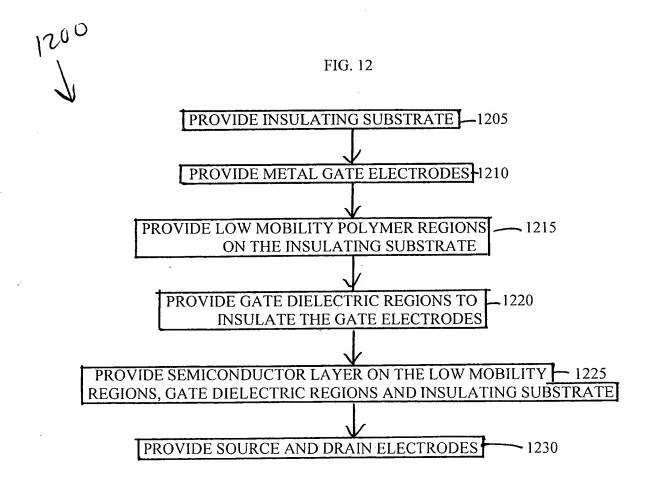
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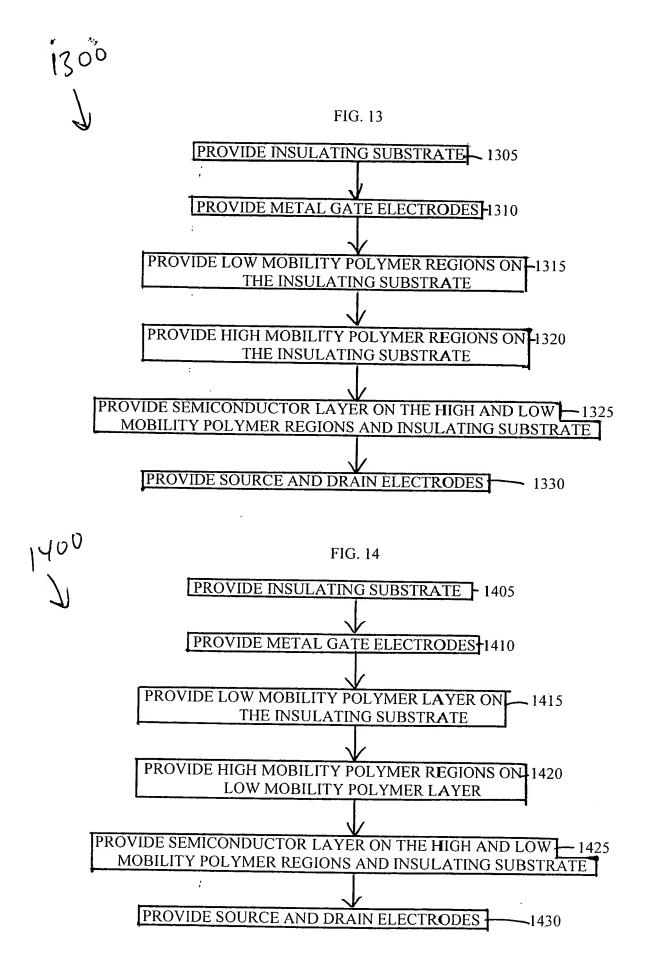


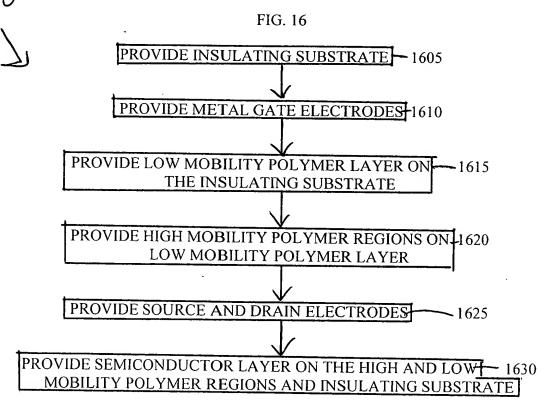
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## 万分男子

substrate T (if not ambient)	60 deg. C 60 deg. C 60 deg. C	80 deg. C		
# samples	<u>†</u> 4	7 -	დო 4	w <b>4</b>
S.D. of mobility V threshold S.D. of Vt on/off ratio subthreshold swing V	9.8 8.7	7.1	5.8 12.6 6.2	24.3 25.5
on/off ratio sul	1260 140	2.00E+03 2670	16 523 1320	19.8 68
S.D. of Vt	8.6 0.3	4.2 NA	4. E. E. 1. 8. 4.	14.7 7.3
V threshold V	-22 -6.7	-19.9 13.9	-14 -2.1	-9.7 -7.1
S.D. of mobility	1.5E+00 3.2E-05	1.50E-01 NA	7.4E-06 1.9E-04 2.3E-03	5.0E-05 1.6E-04
	1.2E+00 1.9E-04 <1E-05	4.80E-01 1.10E+00	5.0E-05 4.1E-04 2.5E-03	5.9E-05 3.4E-04 <1E-05
dielectric	PVPyr 1.2E+00 PVDFMVE 1.9E-04 PBMA <1E-05	PVPhenol 4.80E-01 PVPhenol 1.10E+00	PBMA PVPyr PVDFMVE	PBMA PVPyr PVDFMVE
semiconductor dielectric mobility cm**2/Vs	pentacene pentacene pentacene		2PTTP2 2PTTP2 2PTTP2	DHFTTF DHFTTF DHFTTF